



**THE DATASHEET OF  
IDP30E60XKSA1**



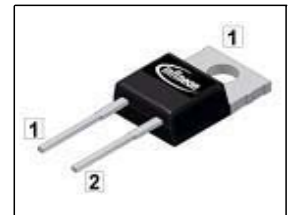
## Fast Switching Diode

### Product Summary

$V_{RRM}$	600	V
$I_F$	30	A
$V_F$	1.5	V
$T_{jmax}$	175	°C

### Features

- 600V diode technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- Easy paralleling
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Qualified according to JEDEC for target applications



Type	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
IDP30E60	PG-TO220-2	-	D30E60	C	A	-

### Maximum Ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	600	V
Continuous forward current $T_C = 25\text{ °C}$ $T_C = 90\text{ °C}$	$I_F$	52.3 34.9	A
Surge non repetitive forward current $T_C = 25\text{ °C}$ , $t_p = 10\text{ ms}$ , sine halfwave	$I_{FSM}$	117	A
Maximum repetitive forward current $T_C = 25\text{ °C}$ , $t_p$ limited by $t_{j,max}$ , $D = 0.5$	$I_{FRM}$	81	A
Power dissipation $T_C = 25\text{ °C}$ $T_C = 90\text{ °C}$	$P_{tot}$	142.9 80.9	W
Operating junction temperature	$T_j$	-40...+175	°C
Storage temperature	$T_{stg}$	-55...+150	
Soldering temperature 1.6mm (0.063 in.) from case for 10 s	$T_S$	260	

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.05	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
SMD version, device on PCB:	$R_{thJA}$				
@ min. footprint		-	-	62	
@ 6 cm <sup>2</sup> cooling area <sup>1)</sup>		-	35	-	

**Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Reverse leakage current	$I_R$				$\mu\text{A}$
$V_R=600\text{V}, T_j=25^\circ\text{C}$		-	-	50	
$V_R=600\text{V}, T_j=150^\circ\text{C}$		-	-	2500	
Forward voltage drop	$V_F$				V
$I_F=30\text{A}, T_j=25^\circ\text{C}$		-	1.5	2	
$I_F=30\text{A}, T_j=150^\circ\text{C}$		-	1.5	-	

<sup>0</sup>J-STD20 and JESD22

<sup>1</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

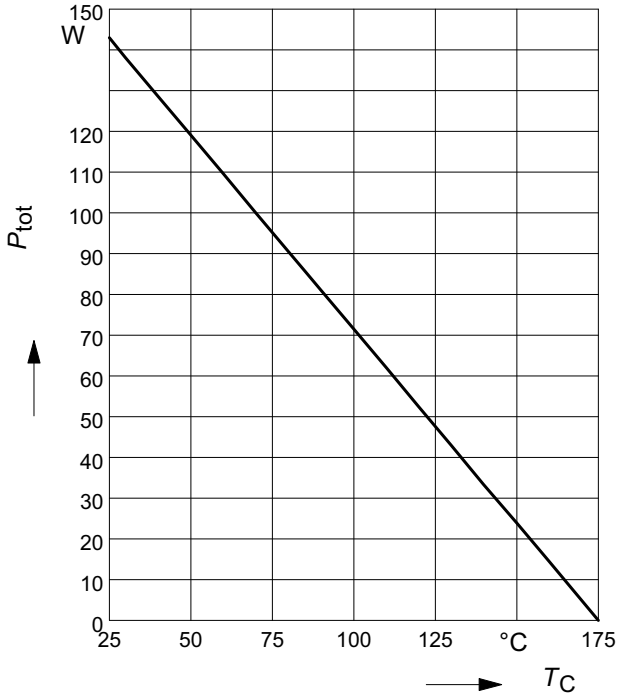
**Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Dynamic Characteristics</b>					
Reverse recovery time $V_R=400\text{V}$ , $I_F=30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=25\text{°C}$ $V_R=400\text{V}$ , $I_F=30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=125\text{°C}$ $V_R=400\text{V}$ , $I_F=30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=150\text{°C}$	$t_{rr}$	-	126 171 178	-	ns
Peak reverse current $V_R=400\text{V}$ , $I_F = 30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=25\text{°C}$ $V_R=400\text{V}$ , $I_F = 30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=125\text{°C}$ $V_R=400\text{V}$ , $I_F = 30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=150\text{°C}$	$I_{rrm}$	-	19 22 24	-	A
Reverse recovery charge $V_R=400\text{V}$ , $I_F=30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=25\text{°C}$ $V_R=400\text{V}$ , $I_F = 30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=125\text{°C}$ $V_R=400\text{V}$ , $I_F = 30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=150\text{°C}$	$Q_{rr}$	-	1100 1950 2150	-	nC
Reverse recovery softness factor $V_R=400\text{V}$ , $I_F=30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=25\text{°C}$ $V_R=400\text{V}$ , $I_F=30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=125\text{°C}$ $V_R=400\text{V}$ , $I_F=30\text{A}$ , $di_F/dt=1000\text{A}/\mu\text{s}$ , $T_j=150\text{°C}$	S	-	4 4.6 4.8	-	

**1 Power dissipation**

$$P_{\text{tot}} = f(T_C)$$

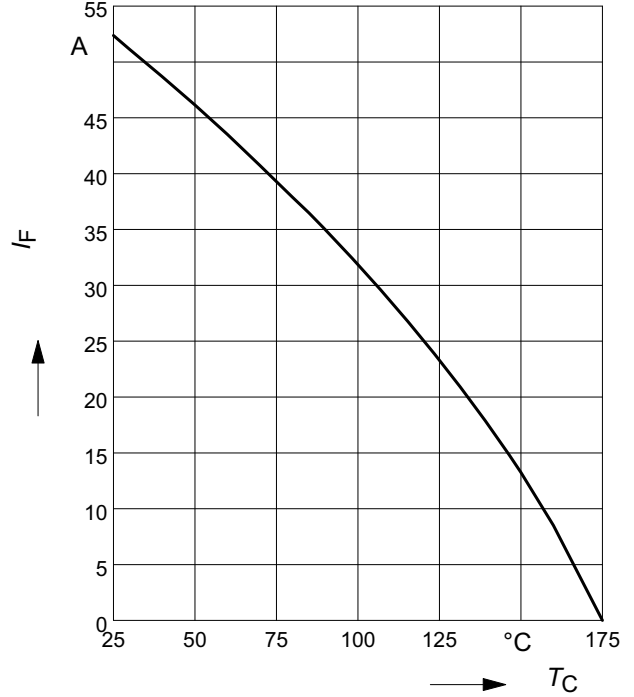
parameter:  $T_j \leq 175^\circ\text{C}$



**2 Diode forward current**

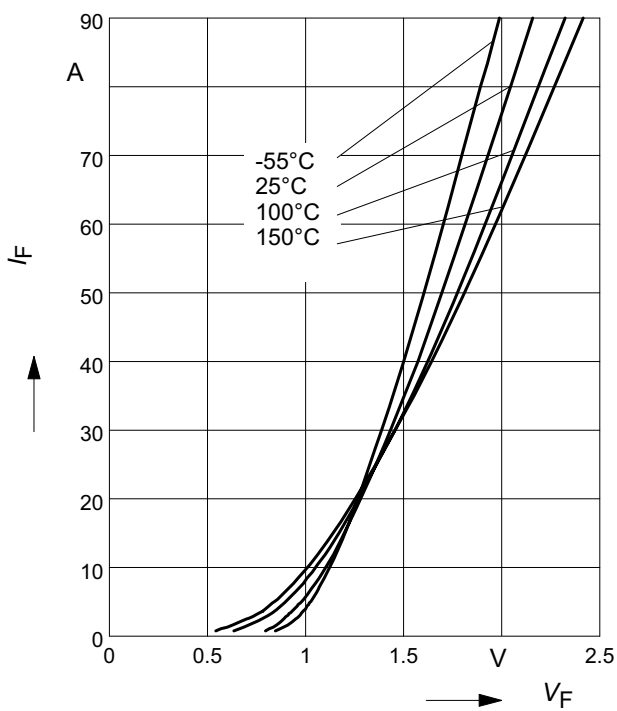
$$I_F = f(T_C)$$

parameter:  $T_j \leq 175^\circ\text{C}$



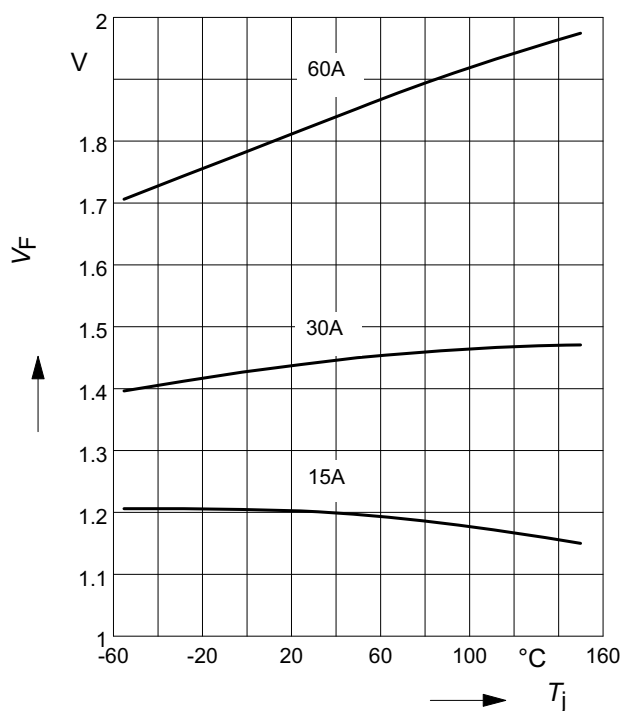
**3 Typ. diode forward current**

$$I_F = f(V_F)$$



**4 Typ. diode forward voltage**

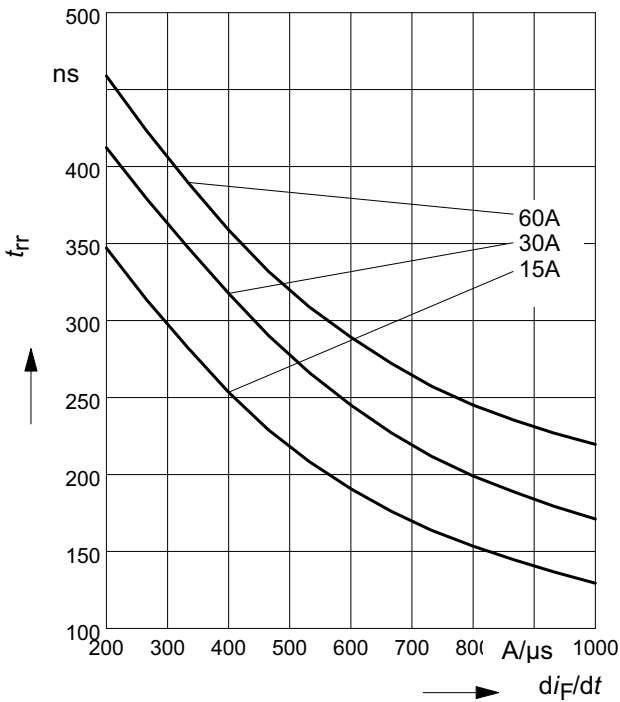
$$V_F = f(T_j)$$



**5 Typ. reverse recovery time**

$$t_{rr} = f(di_F/dt)$$

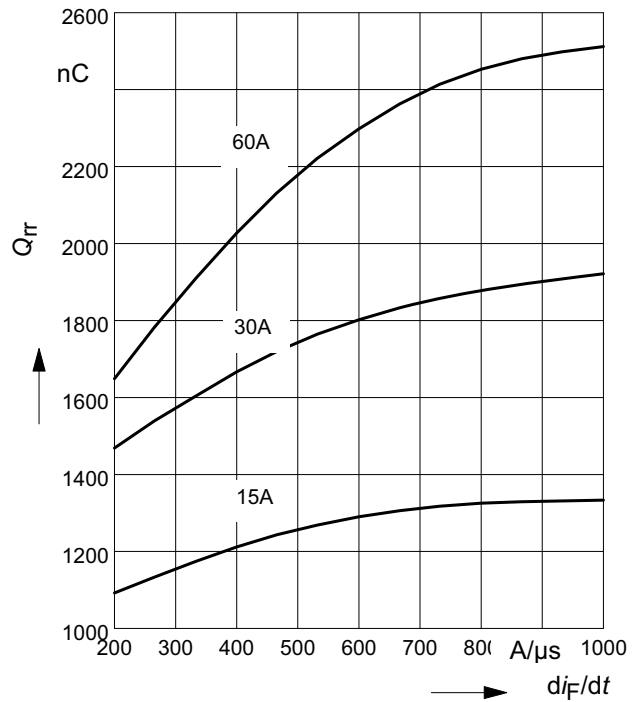
parameter:  $V_R = 400V, T_j = 125^\circ C$



**6 Typ. reverse recovery charge**

$$Q_{rr} = f(di_F/dt)$$

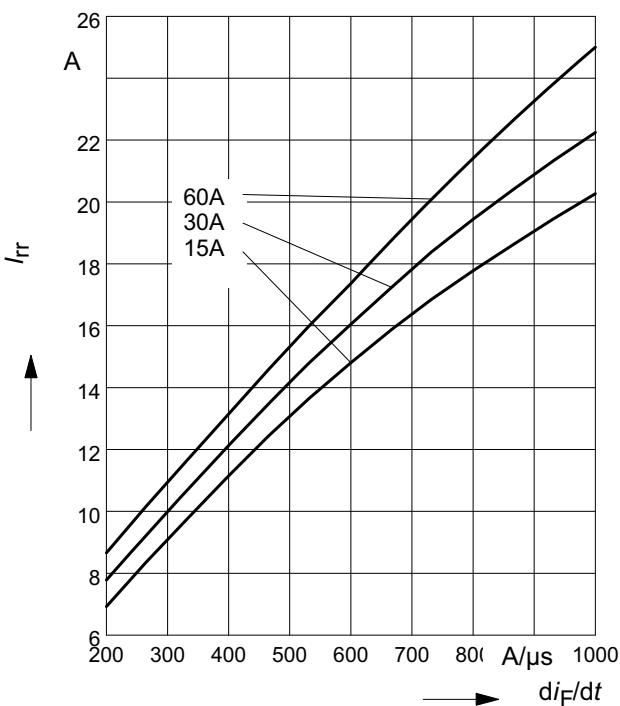
parameter:  $V_R = 400V, T_j = 125^\circ C$



**7 Typ. reverse recovery current**

$$I_{rr} = f(di_F/dt)$$

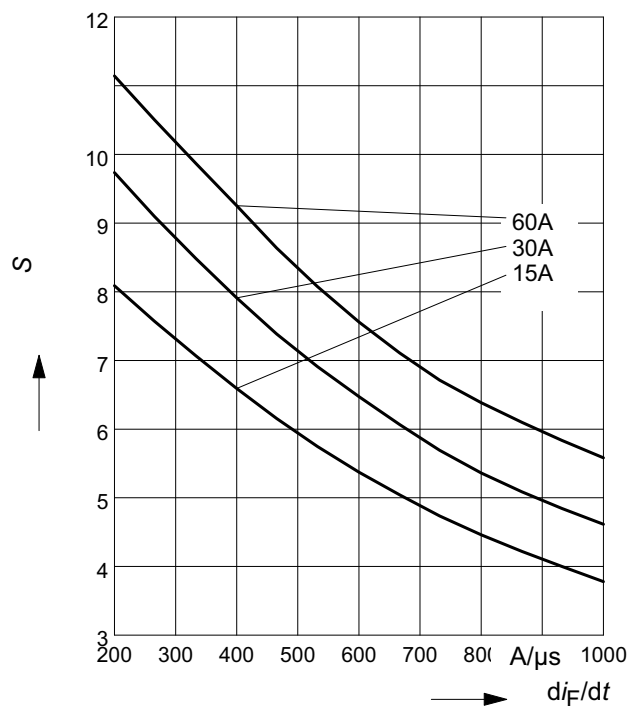
parameter:  $V_R = 400V, T_j = 125^\circ C$



**8 Typ. reverse recovery softness factor**

$$S = f(di_F/dt)$$

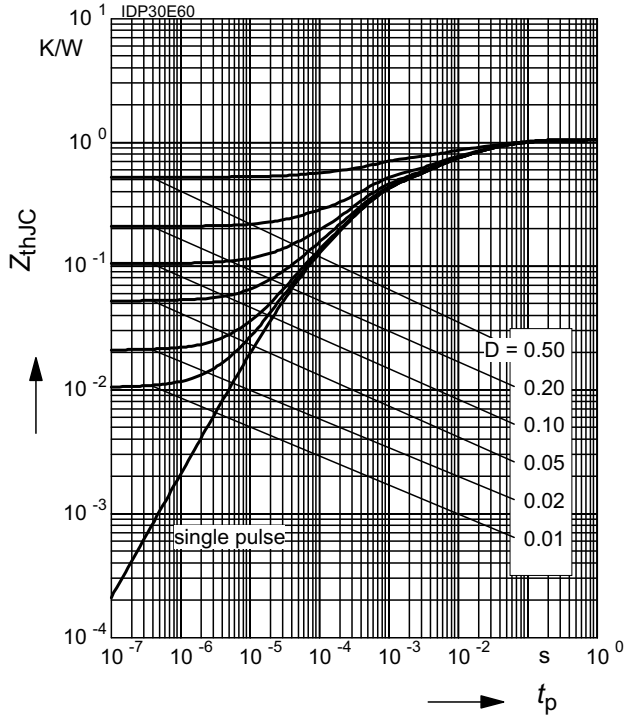
parameter:  $V_R = 400V, T_j = 125^\circ C$

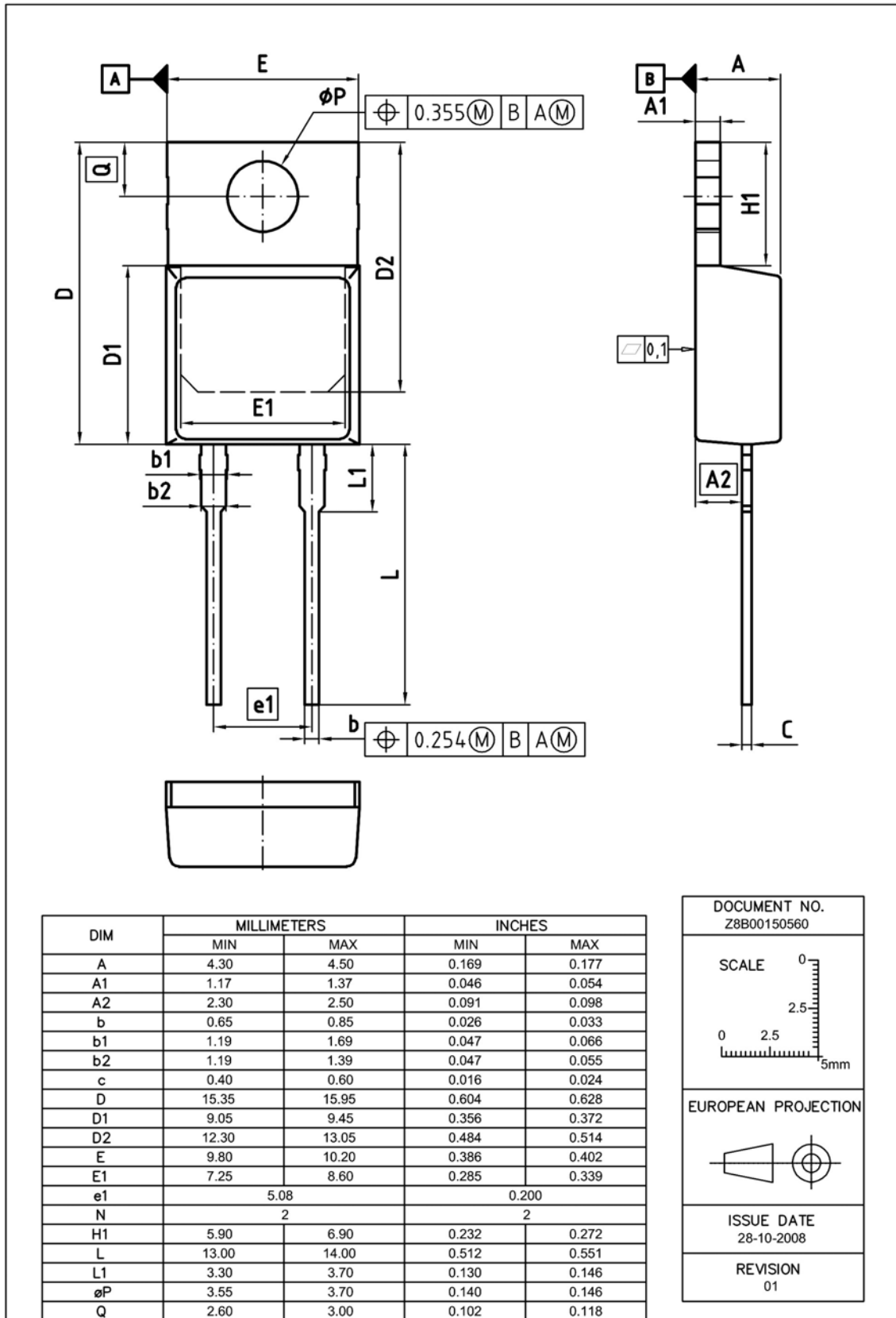


**9 Max. transient thermal impedance**

$$Z_{thJC} = f(t_p)$$

parameter :  $D = t_p/T$





**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
**81726 München, Germany**  
**© 2009 Infineon Technologies AG**  
**All Rights Reserved.**

**Legal Disclaimer**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

**Information**

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

**Warnings**

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

## Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

-  [View IDP30E60XKSA1 on WIN SOURCE](#)
-  [Infineon Technologies Information](#)

## Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management